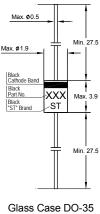
SILICON SCHOTTKY BARRIER DIODE

for various detector, high speed switching

Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal.



Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Average Forward Current	Ι _ο	15	mA
Junction Temperature	TJ	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Current at V _F = 1 V	I _F	3	-	mA
Reverse Current at V _R = 10 V	I _R	-	100	μA
Capacitance at V _R = 1 V, f = 1 MHz	С	-	3	pF
Rectifier Efficiency at V_{in} = 2 Vrms, f = 40 MHz, R _L = 5 KΩ, C _L = 20 pF	η	70	-	%
ESD Capability ¹⁾ at C = 200 pF, both forward and reverse direction 1 pulse.	-	70	-	V

¹⁾ Failure criterion: $I_R \ge 200 \ \mu A$ at $V_R = 10 \ V$







Dated : 20/06/2007

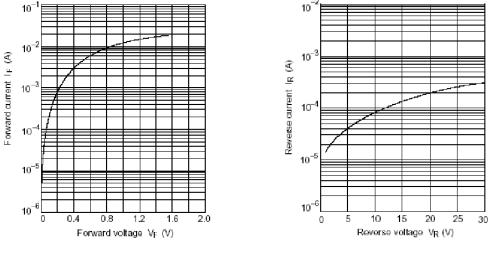
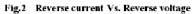


Fig.1 Forward current Vs. Forward voltage



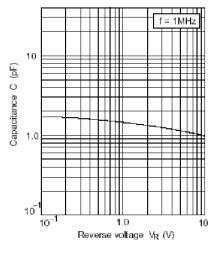


Fig.3 Capacitance Vs. Reverse voltage

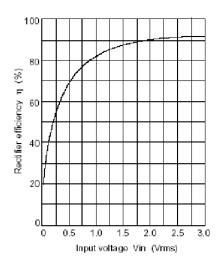


Fig.4 Rectifier efficiency Vs. Input voltage



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